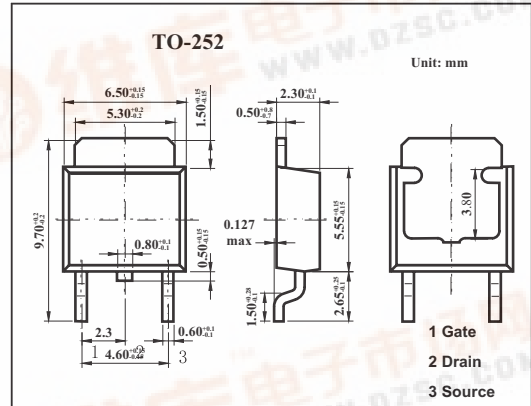


SMD Type MOSFET

MOS Field Effect Transistor
2SK3716

Features

- Super low on-state resistance:
 $R_{DS(on)1} = 6.5\text{ m}\Omega\text{ MAX. (}V_{GS} = 10\text{ V, }I_D = 30\text{ A)}$
 $R_{DS(on)2} = 9.1\text{ m}\Omega\text{ MAX. (}V_{GS} = 4.5\text{ V, }I_D = 30\text{ A)}$
- Low C_{iss} : $C_{iss} = 2700\text{ pF TYP.}$
- Built-in gate protection diode



Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	40	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	± 60	A
	I_{dp}^*	± 240	A
Power dissipation	P_D	$T_a=25^\circ\text{C}$	1.0
		$T_c=25^\circ\text{C}$	84
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10\ \mu\text{s, Duty Cycle} \leq 1\%$

Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=40\text{V, }V_{GS}=0$			10	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 20\text{V, }V_{DS}=0$			± 10	μA
Gate cut off voltage	$V_{GS(off)}$	$V_{DS}=10\text{V, }I_D=1\text{mA}$	1.5	2.0	2.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10\text{V, }I_D=30\text{A}$	22	43		S
Drain to source on-state resistance	$R_{DS(on)1}$	$V_{GS}=10\text{V, }I_D=30\text{A}$		5.2	6.5	$\text{m}\Omega$
	$R_{DS(on)2}$	$V_{GS}=4.5\text{V, }I_D=30\text{A}$		6.6	9.1	$\text{m}\Omega$
Input capacitance	C_{iss}	$V_{DS}=10\text{V, }V_{GS}=0, f=1\text{MHZ}$		2700		pF
Output capacitance	C_{oss}			770		pF
Reverse transfer capacitance	C_{rss}			290		pF
Turn-on delay time	t_{on}			11		ns
Rise time	t_r	$I_D=30\text{A, }V_{GS(on)}=10\text{V, }R_G=0\ \Omega, V_{DD}=20\text{V}$		13		ns
Turn-off delay time	t_{off}			69		ns
Fall time	t_f			14		ns
Total Gate Charge	Q_G		$V_{DD} = 32\text{V}$		50	
Gate to Source Charge	Q_{GS}	$V_{GS} = 10\text{ V}$		9		nC
Gate to Drain Charge	Q_{GD}	$I_D = 60\text{A}$		13		nC

